



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- **ESD** Protected Gate
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

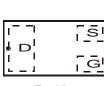
- Case: X1-DFN1006-3 .
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @4)
- Weight: 0.001 grams (Approximate)



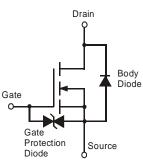
X1-DFN1006-3



Bottom View



Top View Internal Schematic



Equivalent Circuit

Ordering Information (Note 4)	

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN2005LPK-7	DM	7	8	3,000
DMN2005LPK-7B	DM	7	8	10,000
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.				

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-

free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds. 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information

DMN2005LPK-7	From date code 1527 (YYWW), this changes to: Top View Dot Denotes Drain Side Top View Bar Denotes Gate and Source Side Top View Bar Denotes Gate and Source Side
DMN2005LPK-7B	Top View Bar Denotes Gate and Source Side $ \hline + + + + + + + + + + + + + + + + + + $



Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±10	V
Drain Current per element (Note 5)	ID	440	mA

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	450	mW
Thermal Resistance, Junction to Ambient	R _{0JA}	218	°C/W
Operating and Storage Temperature Range	Tj, T _{STG}	-65 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

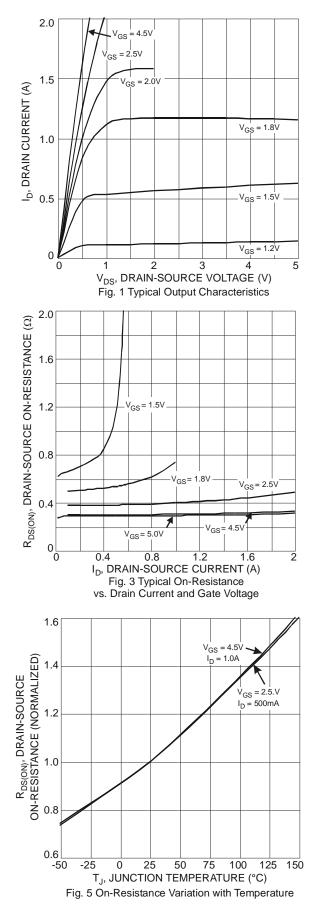
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20			V	$V_{GS} = 0V, I_D = 100 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	10	μA	$V_{DS} = 17V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±5	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.53	_	1.2	V	$V_{DS} = V_{GS}$, $I_D = 100 \mu A$
Static Drain-Source On-Resistance	Rds (ON)		0.35 0.4 0.45 0.55 0.65	1.5 1.7 1.7 3.5 3.5	Ω	$ \begin{array}{l} V_{GS} = 4V, \ I_D = 10 \text{mA} \\ V_{GS} = 2.7 V, \ I_D = 200 \text{mA} \\ V_{GS} = 2.5 V, \ I_D = 10 \text{mA} \\ V_{GS} = 1.8 V, \ I_D = 200 \text{mA} \\ V_{GS} = 1.5 V, \ I_D = 1 \text{mA} \end{array} $
Forward Transfer Admittance	Y _{fs}	40		—	mS	$V_{DS} = 3V, I_{D} = 10mA$

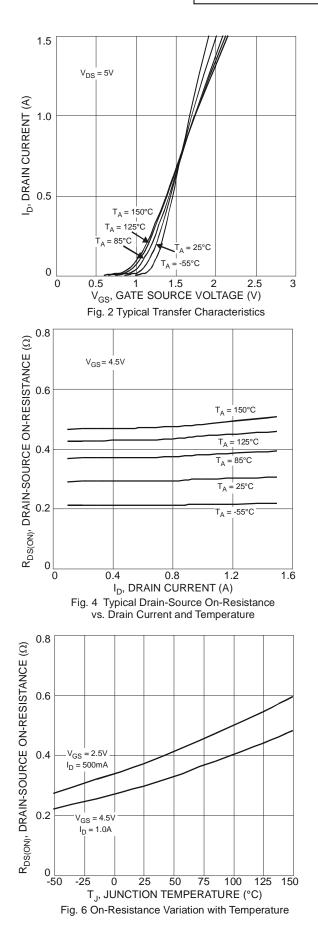
Notes: 5. Device mounted on FR-4 PCB.

6. Short duration pulse test used to minimize self-heating effect.



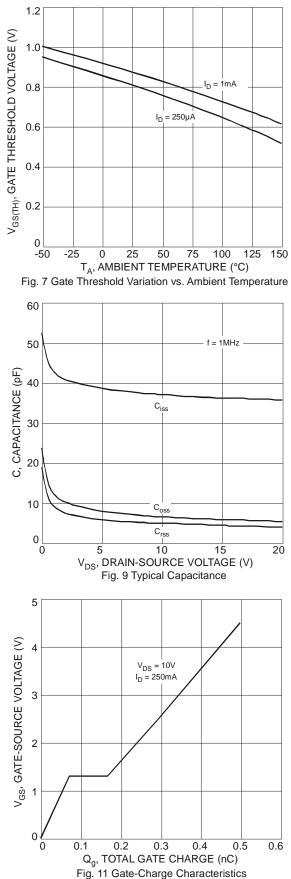
DMN2005LPK

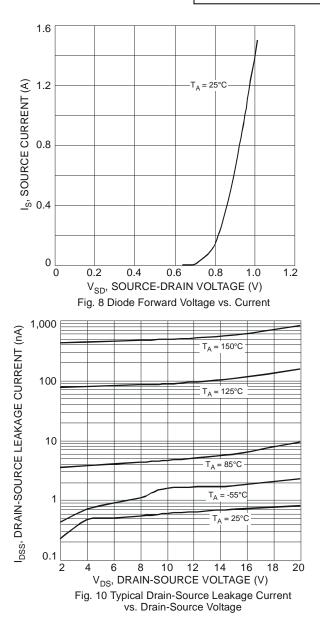




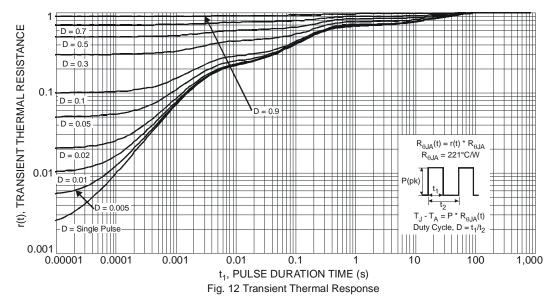


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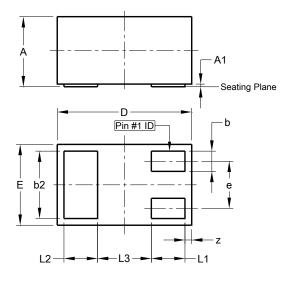






Package Outline Dimensions

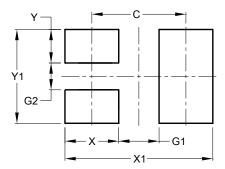
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3				
Dim	Min	Max	Тур	
Α	0.47	0.53	0.50	
A1	0.00	0.05	0.03	
b	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.075	1.00	
Е	0.55	0.675	0.60	
е	-	-	0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3	-	-	0.40	
Z	0.02	0.08	0.05	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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